

Technical Data Data Sheet N0032, Rev. A



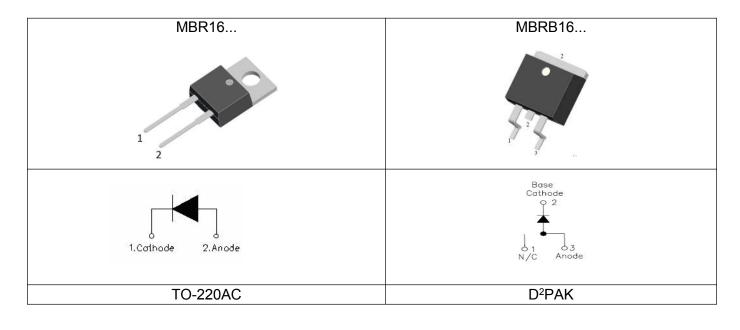
# MBR1635/MBR1645/MBRB1635/MBRB1645 SCHOTTKY RECTIFIER

### Features

- 150<sup>°</sup>C T<sub>J</sub> operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Applications

- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection



### **Maximum Ratings:**

Characteristics	Symbol	Condition		Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage		-	35	(MBR1635)	V
DC Blocking Voltage	V <sub>RWM</sub> VR		45	(MBR1645)	v
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=80°C, rectangular wave form		16	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T_c = 25 $^\circ\!\mathrm{C}$		150	А
Peak Repetitive Reverse Surge Current	I <sub>RRM</sub>	2.0 µ sec 1.0KHz		1.0	А

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Technical Data Data Sheet N0032, Rev. A

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### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@16A, Pulse, T <sub>J</sub> = 25 ℃	0.54	0.63	V
	V <sub>F2</sub>	@16A, Pulse, T <sub>J</sub> = 125 ℃	-	0.57	V
Reverse Current *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 ℃	0.04	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 ℃	20	40	mA
Junction Capacitance	CT	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 ℃ f <sub>SIG</sub> = 1MHz	700	1400	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

\* Pulse width < 300  $\mu$ s, duty cycle < 2%

### Thermal-Mechanical Specifications:

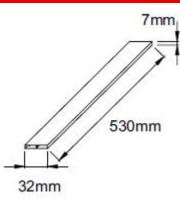
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>0JC</sub>	DC operation	1.5	°C/W
Typical Thermal Resistance Case to Heat Sink	R <sub>0CS</sub>	Mounting surface, smooth and greased(only for TO-220)	0.50	°C/W
Case Style	TO-220ACD <sup>2</sup> PAK			

### **Tube Specification**

Device	Package	Weight	Shipping
MBR16	TO-220AC	1.8g	50pcs / tube
MBRB16	D <sup>2</sup> PAK	1.85g	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### Tube Specification(TO-220AC)





Technical Data Data Sheet N0032, Rev. A

**Ratings and Characteristics Curves** 

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45

#### 100 10000 Junction Capacitance-CT(PF) 10 Reverse Current (MA) TJ=125℃ 1 1000 TJ=25℃ 0.1 0.01 **TJ=25**℃ 100 0.001 0 5 40 10 15 20 25 30 35 20 10 25 30 35 40 15 Reverse Voltage-VR(V) Reverse Voltage (%) **Fig.2-Typical Reverse Characteristics**

Fig.1-Typical Junction Capacitance

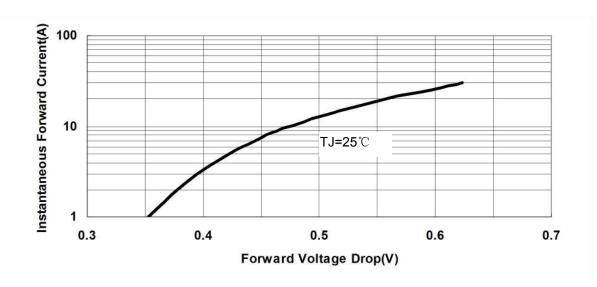


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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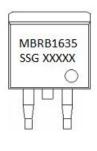


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Technical Data Data Sheet N0032, Rev. A

### **Marking Diagram**

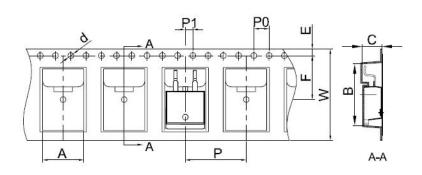




Where XXXXX is YYWWL

MBR B 16 35/45 SSG YY WW	= Device Type = Package type = Forward Current (16A) = Reverse Voltage (35/45V) = SSG = Year = Week
VVVV	
L	= Lot Number
Cautions:	Molding resin Epoxy resin UL:94V-0

**Carrier Tape Specification D<sup>2</sup>PAK** 



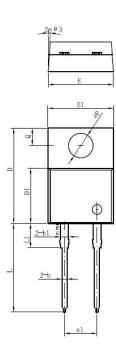
Symbol	Millimeters		
	Min.	Max.	
А	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

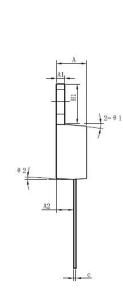


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Technical Data Data Sheet N0032, Rev. A

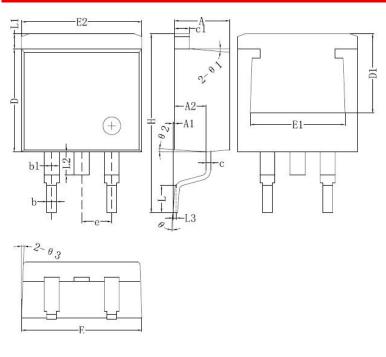
### Mechanical Dimensions TO-220AC





Symbol	Dimensions in millimete		
	Min.	Typical	Max.
Α	4.47	4.70	4.85
A1	1.17	1.27	1.37
A2	2.52	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
C	0.31	0.38	0.61
D	14.64	14.94	15.24
D1	8.50	8.07	8.90
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1	4.98	5.08	5.18
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1	3.56	3.80	3.96
ФР	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

### Mechanical Dimensions D<sup>2</sup>PAK



Symbol	Millimeters			
,	Min.	Min. Typical		
Α	4.47	4.70	4.85	
A1	0	0.10	0.25	
A2	2.59	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
c1	1.17	1.27	1.37	
D	8.50	8.70	8.90	
D1	6.40			
E	10.01	10.16	10.31	
E1	7.6			
E2	9.98	10.08	10.31	
е		2.54		
Н	14.6	15.1	15.6	
L	2.00	2.30	2.74	
L1	1.12	1.27	1.42	
L2	1.30		2.20	
L3		0.25BSC		
е	0	-	8°	
e1		5°		
e2		4°		
e3		4°		

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### Technical Data Data Sheet N0032, Rev. A

### MBR1635/MBRB1635 MBR1645/MBRB1645



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